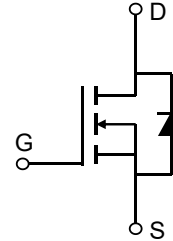


Description

Features

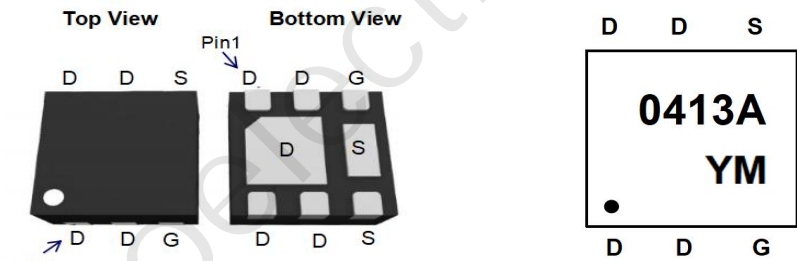
- 40V, 13A
 $R_{DS(ON)}$ Typ = 10.9mΩ @ $V_{GS} = 10V$
 $R_{DS(ON)}$ Typ = 13.5mΩ @ $V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

| Device | Marking | Package | Outline | Reel Size | Reel (pcs) | Per Carton (pcs) |
|-------------|---------|------------|---------|-----------|------------|------------------|
| CRMVTL0413A | 0413A | DFN2020-6L | TAPING | 7" | 3000 | 120000 |

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Value | Units | |
|-----------------------------------|--------------------------------------|------------------------|-------|---|
| V _{DS} | Drain-to-Source Voltage | 40 | V | |
| V _{GS} | Gate-to-Source Voltage | ±20 | V | |
| I _D | Continuous Drain Current | T _C = 25°C | 13 | A |
| | | T _C = 100°C | 7.8 | A |
| I _{DM} | Pulsed Drain Current ⁽¹⁾ | 52 | A | |
| P _D | Power Dissipation | T _C = 25°C | 5 | W |
| R _{θJC} | Thermal Resistance, Junction to Case | 25 | °C/W | |
| T _J , T _{STG} | Junction & Storage Temperature Range | -55 to 150 | °C | |

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|--|--|--|------|------|------|------|
| Off Characteristics | | | | | | |
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | I _D = 250μA, V _{GS} = 0V | 40 | - | - | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 40V, V _{GS} = 0V | - | - | 1.0 | μA |
| I _{GSS} | Gate-Body Leakage Current | V _{DS} = 0V, V _{GS} = ±20V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 1 | 1.3 | 1.8 | V |
| R _{DS(ON)} | Static Drain-Source ON-Resistance ⁽²⁾ | V _{GS} = 10V, I _D = 5A | - | 10.9 | 14.2 | mΩ |
| | | V _{GS} = 4.5V, I _D = 3A | - | 13.5 | 17.6 | mΩ |
| Dynamic Characteristics | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} = 0V, V _{DS} = 20V, f = 1MHz | - | 1172 | - | pF |
| C _{oss} | Output Capacitance | | - | 104 | - | pF |
| C _{rss} | Reverse Transfer Capacitance | | - | 84 | - | pF |
| Q _g | Total Gate Charge | V _{GS} = 0 to 10V V _{DS} = 20V, I _D = 5A | - | 26 | - | nC |
| Q _{gs} | Gate Source Charge | | - | 6 | - | nC |
| Q _{gd} | Gate Drain("Miller") Charge | | - | 5 | - | nC |
| Switching Characteristics | | | | | | |
| t _{d(on)} | Turn-On DelayTime | V _{GS} = 10V, V _{DD} = 20V I _D = 5A, R _{GEN} = 3Ω | - | 7 | - | ns |
| t _r | Turn-On Rise Time | | - | 11 | - | ns |
| t _{d(off)} | Turn-Off DelayTime | | - | 26 | - | ns |
| t _f | Turn-Off Fall Time | | - | 5 | - | ns |
| Drain-Source Diode Characteristics and Max Ratings | | | | | | |
| I _S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | 13 | A |
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 52 | A |
| V _{SD} | Drain to Source Diode Forward Voltage | V _{GS} = 0V, I _S = 5A | - | - | 1.2 | V |
| t _{rr} | Body Diode Reverse Recovery Time | I _F = 5A, di/dt = 100A/us | - | 10 | - | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | | - | 6 | - | nC |

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

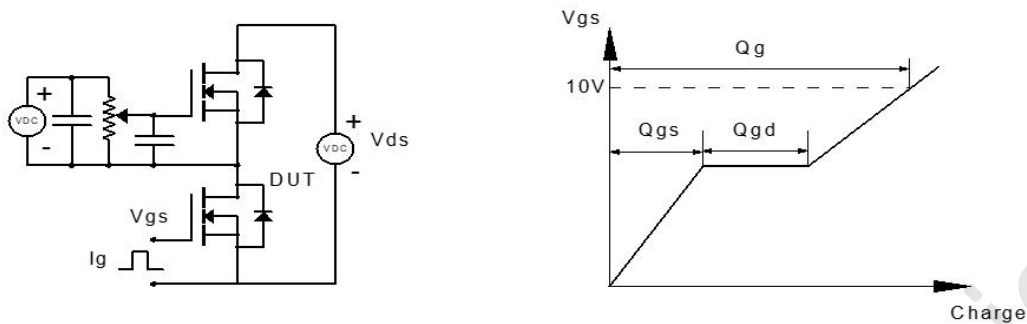


Figure 1: Gate Charge Test Circuit & Waveform

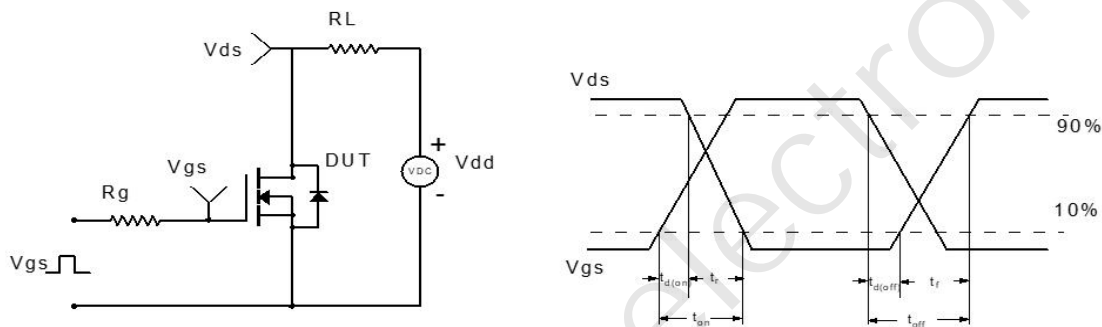


Figure 2: Resistive Switching Test Circuit & Waveform

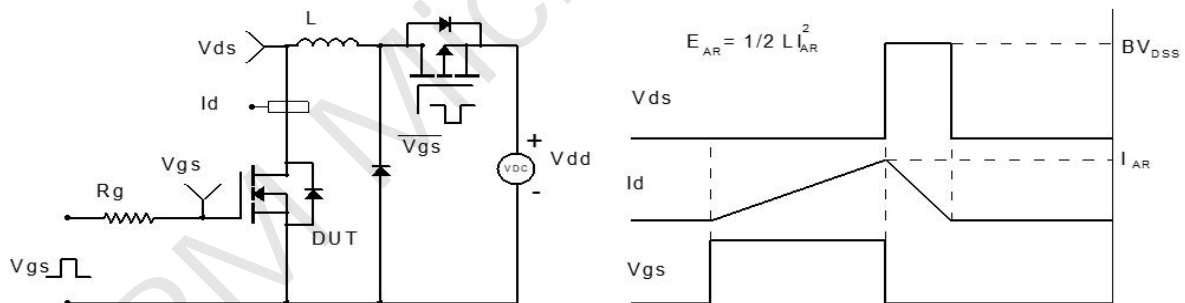


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

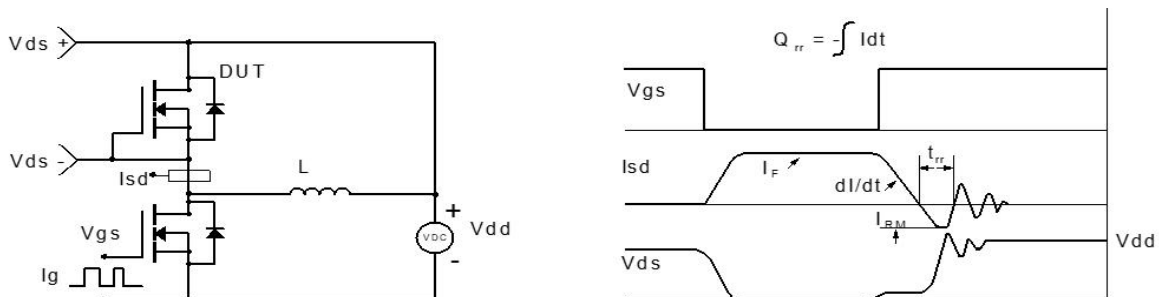
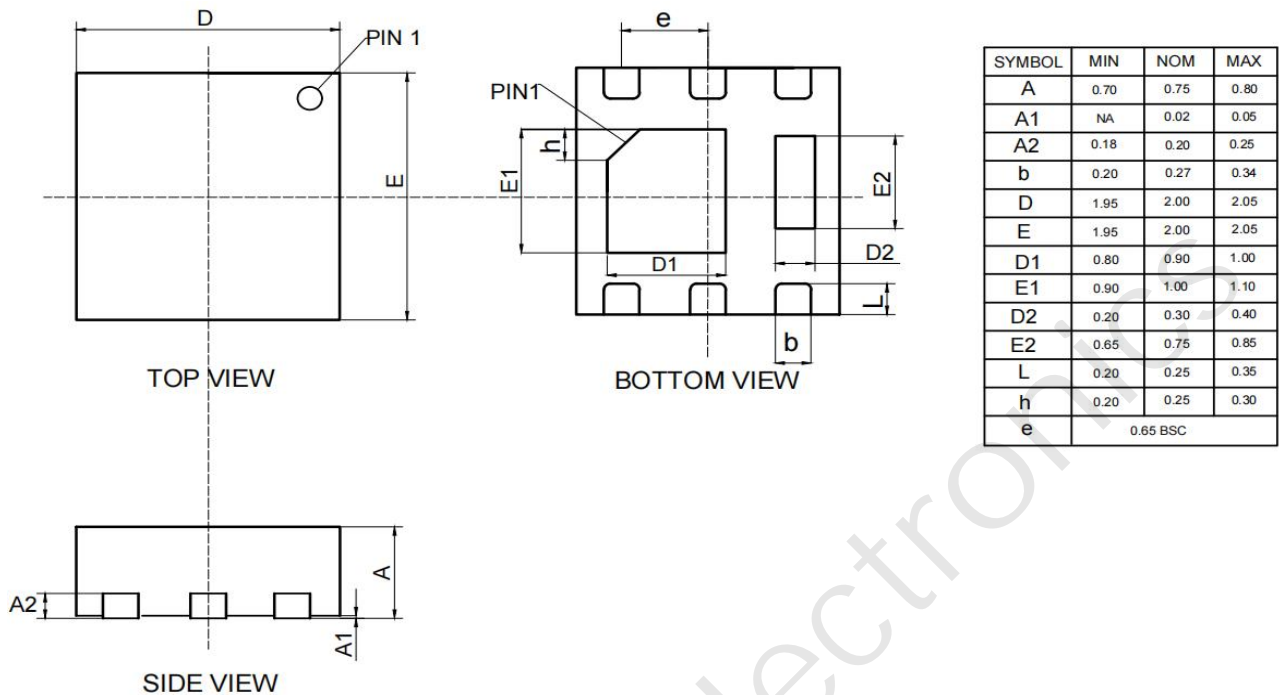


Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(DFN2020-6L)




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Contact information

For more information, please visit: <http://www.crm-semi.tech>

For sales information, please send an email to: sales@crm-semi.com